

Search History. (10 pp.) ~~11~~ (02/17/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	152	tungsten adj silicide near3 barrier and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:12
L2	51	tungsten adj silicide near1 barrier and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 08:10
L3	11247	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413) or (257/908)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/17 08:11
L4	7	3 and tungsten adj silicide near1 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/17 08:12
S1	5	"272,968".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:12
S2	1	"5612249".PN.	USPAT	OR	OFF	2002/05/22 14:58
S3	1	"5637514".PN.	USPAT	OR	OFF	2002/05/22 14:59
S4	1	"5798550".PN.	USPAT	OR	OFF	2002/05/22 14:59
S5	1	"6015736".PN.	USPAT	OR	OFF	2002/05/22 15:00
S6	3	("5306655").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 15:43
S7	3	("5360758").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:03
S8	301	((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and "257"/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 09:41

S9	3	("5382533").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:51
S10	3	("5679968").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:52
S11	3	("5714413").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:53
S12	0	("ep-621632\$-\$\$.did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:53
S13	0	("ep-621632\$-\$\$.did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/22 17:53
S14	0	rajeevakumar.in. and dram adj cell adj structure	EPO	OR	ON	2002/05/22 17:55
S15	6	rajeevakumar.in. and dram adj cell adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/22 17:55
S16	3	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 10:42
S17	0	earom and selection same transistor same dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:43

S18	27	earom and transistor same dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:44
S19	6	earom and transistor same dram. ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:45
S20	109394	earom.ti,ab. and dram.ti,ab. and "257"/\$6.ccls. or "438"/\$6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:46
S21	5	earom.ti,ab. and dram.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:47
S22	187	selection near12 (transistor or fet or mosfet) near12 dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 10:49
S23	44	(selection near6 (transistor or fet or mosfet) near6 dram) and ("257"/\$6.ccls. or "438"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/23 12:09
S24	3	("5854500").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 12:14
S25	2	("6037639").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 13:57
S26	1962	(257/296).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 12:26

S27	1041	(257/401).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 15:08
S28	432	(257/410).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/23 15:08
S29	2	("5885553").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/06 10:35
S30	2	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/06 12:04
S31	0	(side adj wall or sidewall) near12 gate adj oxide near12 silicon adj nitride adj spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 12:06
S32	15	(side adj wall or sidewall) near12 gate adj oxide near12 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 12:07
S33	147	oxidation adj barrier near4 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 13:06
S34	201	(MOS or MOSFET).ti,ab,clm. and silicon adj nitride near4 (sidewall or side adj wall) near4 spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 13:09
S35	3702	((257/296) or (257/401) or (257/410)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/06 16:38

S36	0	((257/296) or (257/401) or (257/410)).CCLS.) and "bird's beak" near4 gate near4 underneath and silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/06 16:39
S37	2	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/04/15 14:10
S38	259	oxide near2 spacer near6 nitride and (mosfet or mos adj device or field adj effect adj transistor).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/15 14:15
S39	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/08 10:23
S40	2	("5612249").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 10:24
S41	2	("5907777").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 11:43
S42	4300	((257/296) or (257/401) or (257/410)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 11:44
S43	8	((257/296) or (257/401) or (257/410)).CCLS.) and "bird's beak"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/10/08 11:44
S44	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/13 16:40

S45	30	(US-5854500-\$ or US-5880496-\$ or US-5969382-\$ or US-6121651-\$ or US-4610078-\$ or US-5473179-\$ or US-5939761-\$ or US-6025215-\$ or US-5907777-\$ or US-5923965-\$ or US-6114735-\$ or US-6127710-\$ or US-5637514-\$ or US-5306655-\$ or US-5360758-\$ or US-6015736-\$ or US-5798550-\$ or US-5612249-\$ or US-6281079-\$ or US-6180978-\$ or US-6037639-\$ or US-5929492-\$ or US-5382533-\$ or US-5714413-\$ or US-5679968-\$ or US-5706164-\$).did. or (US-20030042551-\$ or US-20010041398-\$ or US-20010033006-\$).did. or (JP-05129595-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2004/09/13 16:52
S46	3	((US-5854500-\$ or US-5880496-\$ or US-5969382-\$ or US-6121651-\$ or US-4610078-\$ or US-5473179-\$ or US-5939761-\$ or US-6025215-\$ or US-5907777-\$ or US-5923965-\$ or US-6114735-\$ or US-6127710-\$ or US-5637514-\$ or US-5306655-\$ or US-5360758-\$ or US-6015736-\$ or US-5798550-\$ or US-5612249-\$ or US-6281079-\$ or US-6180978-\$ or US-6037639-\$ or US-5929492-\$ or US-5382533-\$ or US-5714413-\$ or US-5679968-\$ or US-5706164-\$).did. or (US-20030042551-\$ or US-20010041398-\$ or US-20010033006-\$).did. or (JP-05129595-\$).did.) and ahmad. in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 16:52
S47	6	"272968".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/14 17:56
S48	1	"5306655".PN.	USPAT	OR	OFF	2004/09/14 16:48
S49	6	((("5306655") or ("5360655") or ("5612249") or ("5798550") or ("6015736") or ("5637514")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/09/14 17:59
S50	6	((("5306655") or ("5360758") or ("5612249") or ("5798550") or ("6015736") or ("5637514")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/09/14 17:59
S51	6	(US-5798550-\$ or US-6015736-\$ or US-5360758-\$ or US-5612249-\$ or US-5637514-\$ or US-5306655-\$).did.	USPAT	OR	OFF	2004/09/14 18:39

S52	7466	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/09/14 18:40
S53	0	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.) and silicon adj oxide adj passivation adj (layer film) and silicon adj nitride adj spacer and gate adj oxide.ti,ab, clm. and "bird's beak"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/14 18:42
S54	0	((257/288) or (257/296) or (257/321) or (257/344) or (257/368) or (257/401) or (257/408) or (257/410) or (257/411) or (257/412) or (257/413)).CCLS.) and silicon adj oxide near8 passivation adj (layer film) and silicon adj nitride near8 spacer and gate adj oxide.ti,ab, clm. and "bird's beak"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/14 18:42
S55	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 09:07
S56	20	"6037639"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 11:01
S57	21	"5612249"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 11:02
S58	3	((("6037639") or ("5612249") or ("5854500"))).PN.	USPAT	OR	OFF	2005/02/16 15:24
S59	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 12:45

S60	2	isolating near2 metal adj silicide same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:47
S61	42	nitrogen near2 (migration barrier) near10 polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:48
S62	29	nitrogen near2 (migration barrier) near10 polysilicon same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:52
S63	0	nitrogen near2 (migration barrier) near10 polysilicon same gate adj stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:49
S64	427	silicide near3 barrier same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:53
S65	240	(tungsten metal refractory) adj2 silicide near3 barrier same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:54
S66	104	(tungsten metal refractory) adj2 silicide near3 barrier same polysilicon same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:54
S67	5	(tungsten metal refractory) adj2 silicide near3 barrier same polysilicon same gate adj stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:30
S68	373	(tungsten metal refractory) adj2 silicide near3 barrier.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:57
S69	65	(tungsten metal refractory) adj2 silicide near3 barrier.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 12:57

S70	131	gate adj stack and tungsten adj silicide near4 gate and polysilicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:27
S71	15	gate adj stack and ("WSi.sub."42" tungsten adj silicide) near10 barrier near10 gate and polysilicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:28
S72	2	("5414301").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:31
S73	1	S72 and tungsten and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:32
S74	0	S72 and tungsten near8 barrier near8 silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:37
S75	6	"885553".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:39
S76	65	gate adj stack and tungsten adj silicide near10 gate near10 polysilicon near10 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 15:40
S77	7	gate adj stack and tungsten adj silicide near8 gate near8 polysilicon near8 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:42
S78	1	gate adj stack and tungsten adj silicide near8 gate near8 polysilicon near8 silicon adj nitride and refractory adj metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:43
S79	1	gate adj stack and tungsten adj silicide near8 gate near8 polysilicon near8 silicon adj nitride and refractory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:43

S80	1	gate adj stack and tungsten adj silicide near10 gate near10 polysilicon near10 silicon adj nitride and refractory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:45
S81	103	(tungsten adj silicide "WSi.sub. "\$2) near4 barrier and (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:46
S82	72	(tungsten adj silicide "WSi.sub. "\$2) near2 barrier and (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:46
S83	27	(tungsten adj silicide "WSi.sub. "\$2) near2 barrier adj layer and (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 15:56
S84	1	metal adj diffusion adj barrier.ti.	IBM_TDB	OR	ON	2005/02/16 15:56